

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended): A laser submount on top of which a laser is mounted, comprising:

a substrate; and

a lens above the substrate and below the laser. ~~and~~

~~a laser above the substrate.~~

Claim 2 (original): The laser submount of claim 1, wherein the substrate is selected from the group consisting of silicon, quartz, sodium borosilicate glass, sapphire, gallium arsenide, silicon carbide, and gallium phosphide.

Claim 3 (currently amended): The laser submount of claim 1, further comprising:

a planarization layer covering the lens; and

an interconnect ~~layer~~ above the planarization layer.

Claim 4 (original): The laser submount of claim 3, wherein the planarization layer is an oxide layer.

Claim 5 (currently amended): The laser submount of claim 3, further comprising:

a dielectric layer ~~above~~ covering the interconnect ~~layer~~; and

a contact pad above the dielectric layer, wherein the laser is electrically connected to the contact pad.

Claim 6 (original): The laser submount of claim 5, further comprising:

a sealing ring above the dielectric layer and surrounding the contact pad and the laser.

Claim 7 (original): The laser submount of claim 1, further comprising:

at least one of a passive integrated circuit and an active integrated circuit.

Claim 8 (withdrawn): A method for forming a laser submount, comprising:

forming a lens above a substrate; and

mounting a laser to the laser submount above the substrate.

Claim 9 (withdrawn): The method of claim 8, wherein the substrate is selected from the group consisting of silicon, quartz, sodium borosilicate glass, sapphire, gallium arsenide, silicon carbide, and gallium phosphide.

Claim 10 (withdrawn): The method of claim 8, further comprising, subsequent to said forming a lens and prior to said mounting a laser:

forming a planarization layer covering the lens; and

forming an interconnect layer above the planarization layer.

Claim 11 (withdrawn): The method of claim 10, wherein the planarization layer is an oxide layer.

Claim 12 (withdrawn): The method of claim 10, further comprising, subsequent to said forming an interconnect layer and prior to said mounting a laser:

forming a dielectric layer covering the interconnect layer; and

forming a contact pad above the dielectric layer, wherein the laser is electrically connected to the contact pad.

Claim 13 (withdrawn): The method of claim 12, further comprising, subsequent to said forming a dielectric and prior to said mounting a laser:

forming a sealing ring above the dielectric layer and surrounding the contact pad and the laser.

Claim 14 (withdrawn): The method of claim 8, further comprising:

forming at least one of a passive integrated circuit and an active integrate circuit above the substrate.

Claim 15 (new): The laser submount of claim 5, further comprising:

a plug electrically connecting the interconnect and the contact pad.

Claim 16 (new): The laser submount of claim 6, further comprising:

- a first plug electrically connecting the interconnect and the contact pad;
- another contact pad above the dielectric layer and outside of the seal ring; and
- a second plug electrically connecting the interconnect and the another contact pad.